

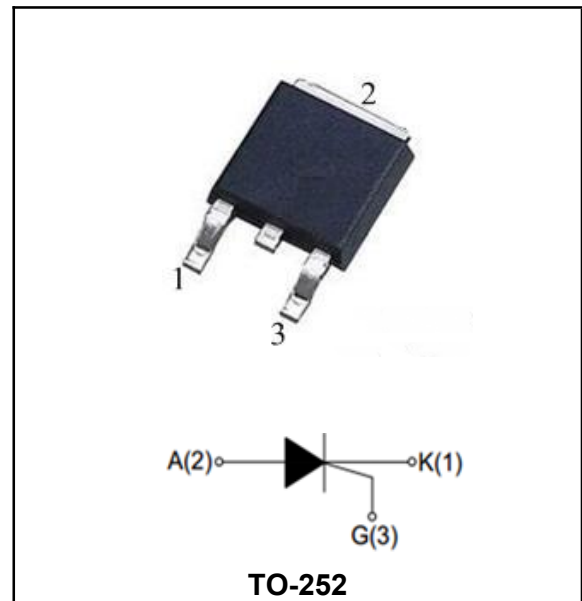
2A Standard SCRs

Product Summary

Symbol	Value	Unit
$I_{T(AV)}$	2	A
$V_{DRM} V_{RRM}$	600/800	V
V_{TM}	1.55	V

Features

With high ability to withstand the shock loading of large current, Provide high dv/dt rate with strong resistance to electromagnetic interference



Application

Power charger, T-tools, massager, solid staterelay, AC Motor speed regulation and so on.

Order Information

Part Number	Package	Marking	Packing	Packing Quantity
2P4M	TO-252	2P4M XXXX	Tape	3000PCS/Tape

Absolute maximum ratings (Ta=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Repetitive peak off-state voltage	V_{DRM}	600/800	V
Repetitive peak reverse voltage	V_{RRM}	600/800	V
Average on-state current	$I_{T(AV)}$	2	A
RMS on-state current	$I_{T(RMS)}$	3	A
Non repetitive surge peak on-state current	I_{TSM}	20	A
I^2t value for fusing (tp=10ms)	I^2t	2	A ² S
Critical rate of rise of on-state current	dI_T/dt	50	A/μs
Peak gate current (tp=20us, Tj=110°C)	I_{GM}	0.2	A
Average gate power dissipation (Tj=110°C)	$P_G (AV)$	0.1	W
Junction Temperature	T_J	-40-+110	°C
Storage Temperature	T_{STG}	-40 ~+150	°C

Electrical characteristics (TA=25°C, unless otherwise noted)

Parameter	Symbol	Test Condition	Value			Unit
			Min	Typ	Max	
Gate trigger current	I_{GT}	V _D =6V, R _L =100Ω, R _{GK} =1kΩ	10	-	200	μA
Gate trigger voltage	V_{GT}	V _D =12V, R _L =100Ω, R _{GK} =1kΩ	-	-	0.8	v
Gate non-trigger voltage	V_{GD}	V _D =1/2V _{DRM} , R _{GK} =1kΩ, T _J =110°C	0.2	-	-	v
Holding current	I_H	V _D =24V, R _{GK} =1kΩ, I _{TM} =4A, T _J =25°C	-	1	3	mA
latching current	I_L	I _G =1.2I _{GT}	-	-	4	mA
Critical-rate of rise of commutation voltage	dVb/dt	V _D =2/3V _{DRM} , R _{GK} =1kΩ, T _J =110°C	10	-	-	V/μs

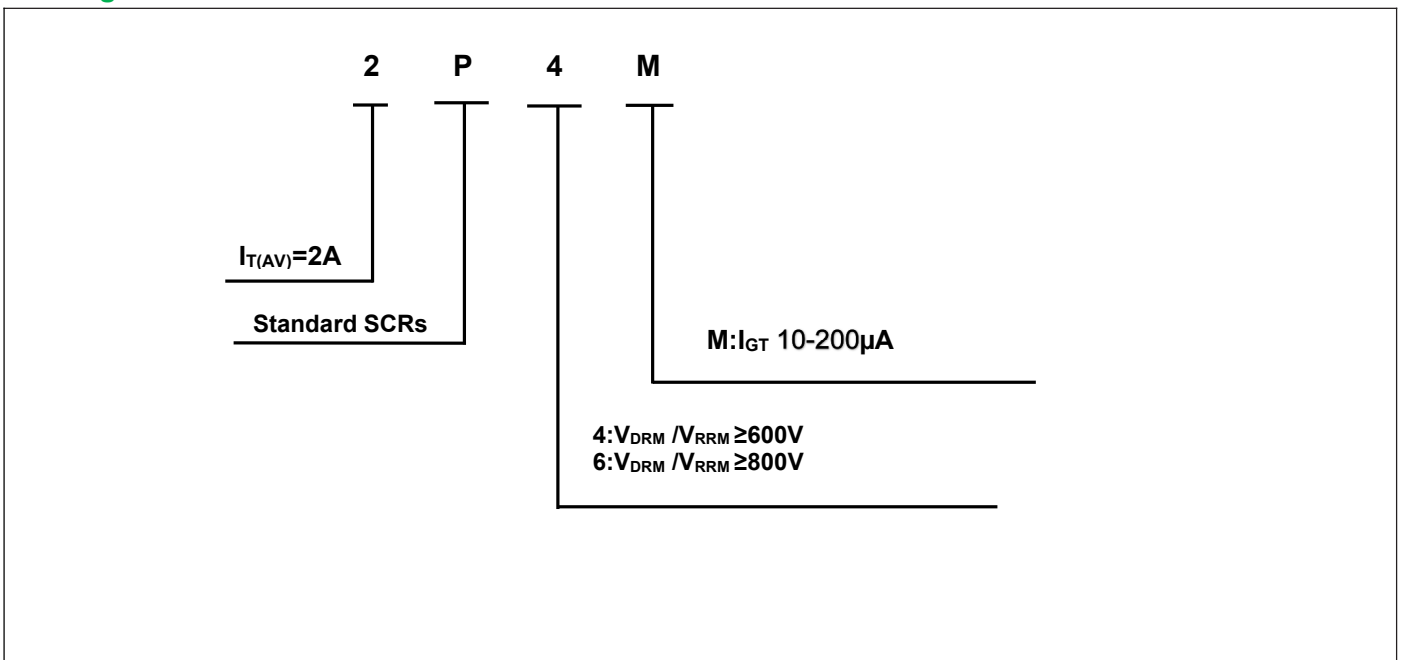
STATIC CHARACTERISTICS

Forward "on" voltage	V_{TM}	I _{TM} =4A	-	-	1.55	V
Repetitive Peak Off-State Current	I_{DRM}	V _D =V _{DRM} /V _{RRM} , T _J =25°C	-	-	5	μA
Repetitive Peak Reverse Current	I_{RRM}	V _D =V _{DRM} /V _{RRM} , T _J =110°C	-	-	100	μA

THERMAL RESISTANCES

Thermal resistance	Rth(j-c)	Junction to case		TYP.	6.5	°C/W
	Rth(j-a)	Junction to ambient	S=0.5cm ²	TYP.	70	°C/W

Ordering Information



Typical Characteristics

FIG.1: Maximum power dissipation versus RMS on-state current (full cycle)

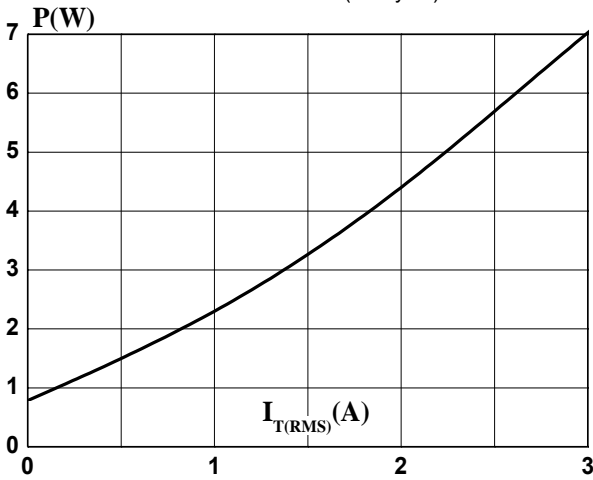


FIG.2: RMS on-state current versus case temperature (full cycle)

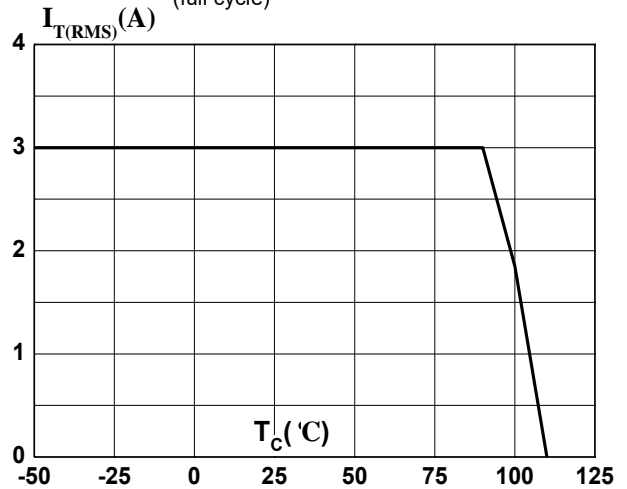


FIG.3: Surge peak on-state current versus number of cycles

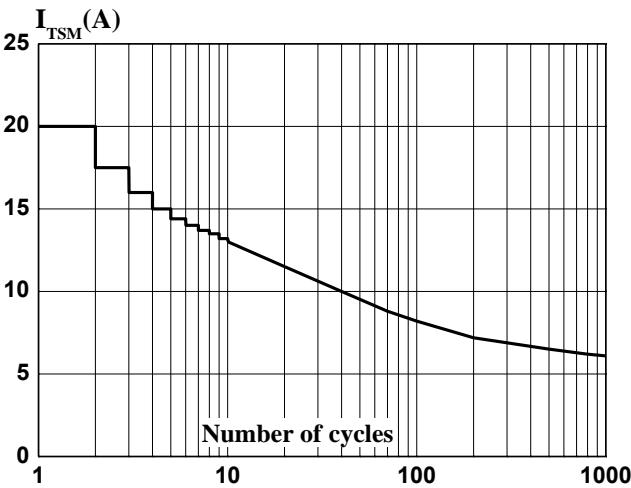


FIG.4: On-state characteristics (maximum values)

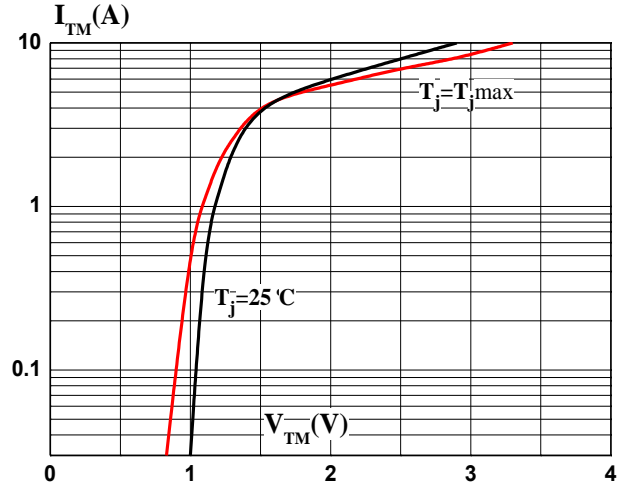


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 10\text{ms}$

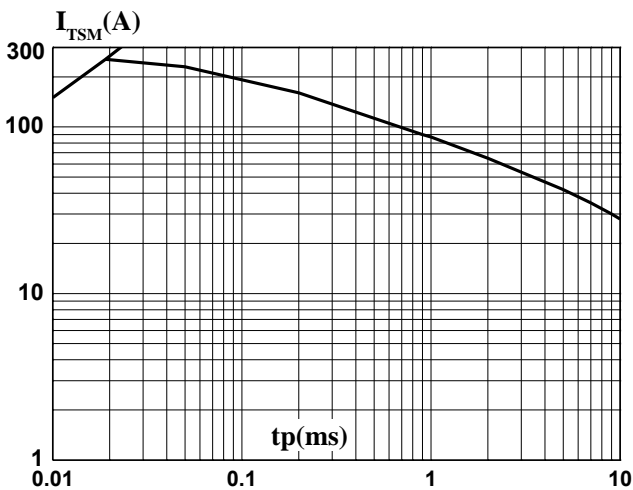
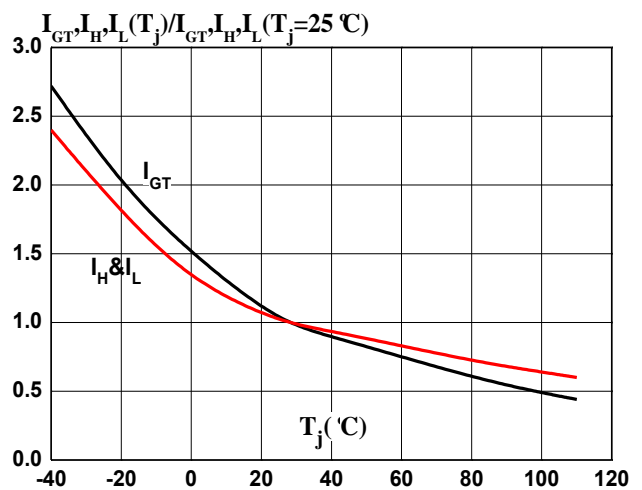
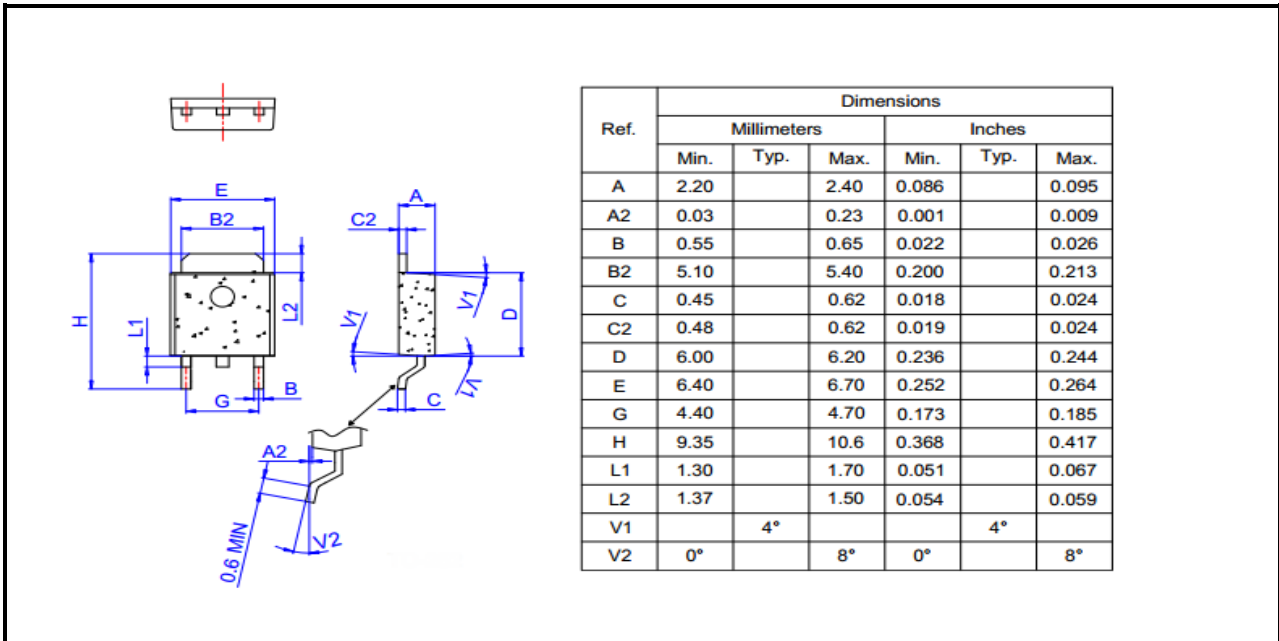


FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature (typical values)



Package Information

TO-252



单击下面可查看定价，库存，交付和生命周期等信息

[>>YFW\(佑风微\)](#)